

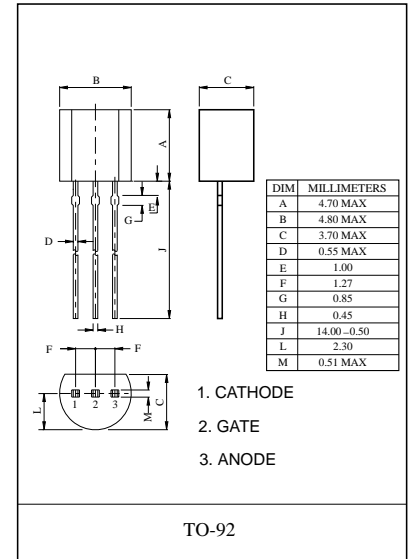
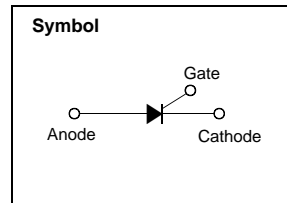
### Silicon Planar PNP Thyristor

#### MAIN FEATURES

Symbol	Value	Unit	
$I_{T(RMS)}$	0.8	A	
$V_{DRM}/V_{RRM}$	MCR100-6/F	400	V
	MCR100-8/F	600	
$T_J$	Junction Temperature	-40 to 125	°C
$T_{stg}$	Storage Temperature	-55 to 150	°C

#### DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

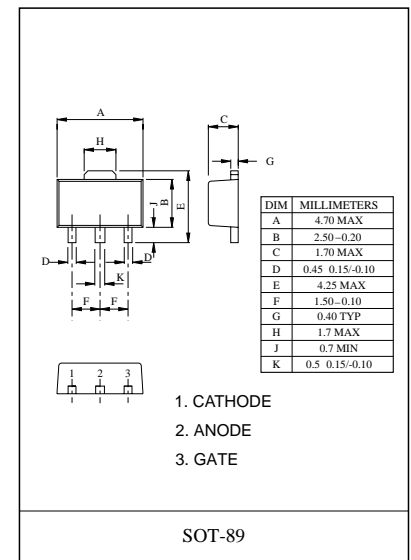


#### FEATURES

- Blocking voltage to 400 V (MCR100-6/F) , 600V (MCR100-8/F)
- RMS on-state current to 0.8 A
- General purpose switching

#### APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays.



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT	
On state voltage *	$V_{TM}$	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	$V_{GT}$	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward and reverse blocking voltage	$V_{DRM}$ AND $V_{RRM}$	$I_{DRM}= 10 \mu A$	400 600		V	
Peak forward or reverse blocking current	$I_{DRM}$ $I_{RRM}$	$V_{AK}= \text{Rated}$ $V_{DRM}$ or $V_{RRM}$		10	$\mu A$	
Holding current	$I_H$	$I_{HL}=20mA, V_{AK}=7V$		5	mA	
Gate trigger current	$I_{GT}$	$V_{AK}=7V$	A2	5	15	$\mu A$
			A1	15	30	$\mu A$
			A	30	80	$\mu A$
			B	80	200	$\mu A$

\* Forward current applied for 1 ms maximum duration, duty cycle  $\leq 1\%$ .

## Typical Characteristics

